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FIRST SEMESTER (CBCSS—UG) DEGREE EXAMINATION NOVEMBER 2021

(CBCSS)

Electronics

ELE 1C 01—ELECTRONIC DEVICES

(2021 Admissions)

Time: Two Hours

Maximum: 60 Marks

Section A

Answer at least eight questions.

Each question carries 3 marks.

All questions can be attended.

Overall Ceiling 24.

- 1. Differentiate with active and passive devices.
- 2. What is base spreading resistance?
- 3. Explain different types of relays.
- 4. What is a photodiode?
- 5. What is an unbiased transistor?
- 6. Explain about intrinsic semiconductors.
- 7. Explain the structure of MOSFET.
- 8. Explain intrinsic standoff ratio.
- 9. What is a transistor? Give its applications.
- 10. Mention the applications of JFET.
- 11. Define thermal run away.
- 12. Differentiate between bipolar and uni-polar devices.

 $(8 \times 3 = 24 \text{ marks})$

Turn over

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Section B

Answer at least **five** questions.

Each question carries 5 marks.

All questions can be attended.

Overall Ceiling 25.

- 13. Explain the current gain of a transistor in CE configuration.
- 14. Briefly explain about different types of resistors.
- 15. Compare between BJT and JFET.
- 16. What are the JFET parameters? Explain them.
- 17. Explain the operation of LDR.
- 18. With the help of energy band theory, define conductors, insulators and semi-conductors.
- 19. Explain about the leakage current concept in the common base BJT.

 $(5 \times 5 = 25 \text{ marks})$

Section C

Answer any one question.

The question carries 11 marks.

- 20. Explain about PN junction diode. Draw its symbol and V-I characteristics.
- 21. Explain the working of UJT as a relaxation oscillator.

 $(1 \times 11 = 11 \text{ marks})$